Datablad till Digital Elektronik

Innehåll

Belganet Dataelektronik www.bde.se

Datablad 74LS00

FAIRCHILD SEMICONDUCTOR™

August 1986
Revised March 2000

DM74LS00
Quad 2-Input NAND Gate

General Description

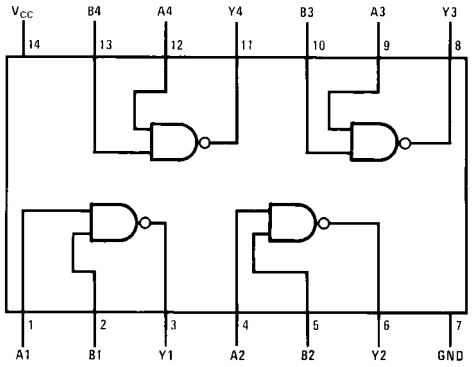
This device contains four independent gates each of which performs the logic NAND function.

Ordering Code:

Order Number	Package Number	Package Description
DM74LS00M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
DM74LS00SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
DM74LS00N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram



Function Table

$Y = \overline{AB}$

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H = HIGH Logic Level
L = LOW Logic Level

 DS006439

Absolute Maximum Ratings(Note 1)

Supply Voltage	7V
Input Voltage	7V
Operating Free Air Temperature Range	0°C to +70°C
Storage Temperature Range	−65°C to +150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Recommended Operating Conditions

Symbol	Parameter	Min	Nom	Max	Units
V_{CC}	Supply Voltage	4.75	5	5.25	V
V_{IH}	HIGH Level Input Voltage	2			V
V_{IL}	LOW Level Input Voltage			0.8	V
I_{OH}	HIGH Level Output Current			−0.4	mA
I_{OL}	LOW Level Output Current			8	mA
T_A	Free Air Operating Temperature	0		70	°C

Electrical Characteristics

over recommended operating free air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ (Note 2)	Max	Units
V_I	Input Clamp Voltage	V_{CC} = Min, I_I = −18 mA			−1.5	V
V_{OH}	HIGH Level Output Voltage	V_{CC} = Min, I_{OH} = Max, V_{IL} = Max	2.7	3.4		V
V_{OL}	LOW Level Output Voltage	V_{CC} = Min, I_{OL} = Max, V_{IH} = Min		0.35	0.5	V
		I_{OL} = 4 mA, V_{CC} = Min		0.25	0.4	
I_I	Input Current @ Max Input Voltage	V_{CC} = Max, V_I = 7V			0.1	mA
I_{IH}	HIGH Level Input Current	V_{CC} = Max, V_I = 2.7V			20	μA
I_{IL}	LOW Level Input Current	V_{CC} = Max, V_I = 0.4V			−0.36	mA
I_{OS}	Short Circuit Output Current	V_{CC} = Max (Note 3)	−20		−100	mA
I_{CCH}	Supply Current with Outputs HIGH	V_{CC} = Max		0.8	1.6	mA
I_{CCL}	Supply Current with Outputs LOW	V_{CC} = Max		2.4	4.4	mA

Note 2: All typicals are at V_{CC} = 5V, T_A = 25°C.

Note 3: Not more than one output should be shorted at a time, and the duration should not exceed one second.

Switching Characteristics

at V_{CC} = 5V and T_A = 25°C

Symbol	Parameter	R_L = 2 kΩ				Units
		C_L = 15 pF		C_L = 50 pF		
		Min	Max	Min	Max	
t_{PLH}	Propagation Delay Time LOW-to-HIGH Level Output	3	10	4	15	ns
t_{PHL}	Propagation Delay Time HIGH-to-LOW Level Output	3	10	4	15	ns

Datablad 74HC00

FAIRCHILD SEMICONDUCTOR™

September 1983
Revised February 1999

MM74HC00
Quad 2-Input NAND Gate

General Description

The MM74HC00 NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 74HC logic family is functionally as well as pin-out compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 8 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20 μA maximum (74HC Series)
- Low input current: 1 μA maximum
- Fanout of 10 LS-TTL loads

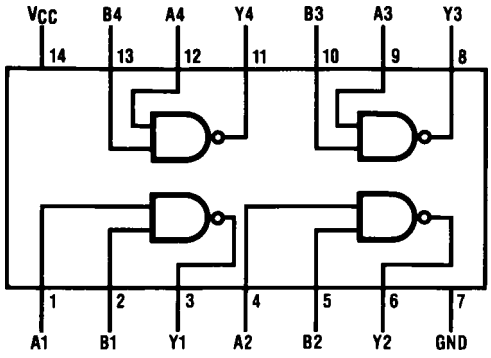
Ordering Code:

Order Number	Package Number	Package Description
MM74HC00M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150” Narrow
MM74HC00SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC00MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC00N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300” Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter “X” to the ordering code.

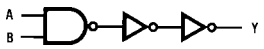
Connection Diagram

Pin Assignments for DIP, SOIC, SOP and TSSOP



Top View

Logic Diagram



Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC}+1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC}+0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temperature Range (T_A)	−40	+85	°C
Input Rise or Fall Times			
(t_r, t_f) V_{CC} = 2V		1000	ns
V_{CC} = 4.5V		500	ns
V_{CC} = 6.0V		400	ns

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C.

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum HIGH Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum LOW Level Input Voltage		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum HIGH Level Output Voltage	V_{IN} = V_{IH} or V_{IL}						
		$\|I_{OUT}\| \le 20$ μA	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IH} or V_{IL}						
		$\|I_{OUT}\| \le 4.0$ mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum LOW Level Output Voltage	V_{IN} = V_{IH}						
		$\|I_{OUT}\| \le 20$ μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH}						
		$\|I_{OUT}\| \le 4.0$ mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		2.0	20	40	μA

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics

V_{CC} = 5V, T_A = 25°C, C_L = 15 pF, t_r = t_f = 6 ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		8	15	ns

AC Electrical Characteristics

V_{CC} = 2.0V to 6.0V, C_L = 50 pF, t_r = t_f = 6 ns (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C		T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	45	90	113	134	ns
			4.5V	9	18	23	27	ns
			6.0V	8	15	19	23	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Datablad 4011

CD4001BM/CD4001BC Quad 2-Input NOR Buffered B Series Gate
CD4011BM/CD4011BC Quad 2-Input NAND Buffered B Series Gate

National Semiconductor

March 1988

CD4001BM/CD4001BC Quad 2-Input NOR Buffered B Series Gate
CD4011BM/CD4011BC Quad 2-Input NAND Buffered B Series Gate

General Description

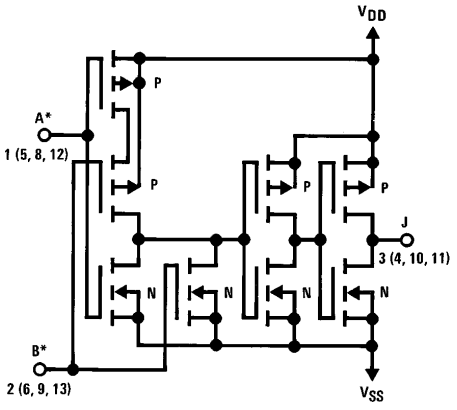
These quad gates are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. They have equal source and sink current capabilities and conform to standard B series output drive. The devices also have buffered outputs which improve transfer characteristics by providing very high gain.

All inputs are protected against static discharge with diodes to V_{DD} and V_{SS}.

Features

Low power TTL compatibility	Fan out of 2 driving 74L or 1 driving 74LS
5V–10V–15V parametric ratings	
Symmetrical output characteristics	
Maximum input leakage 1	A at 15V over full temperature range

Schematic Diagrams



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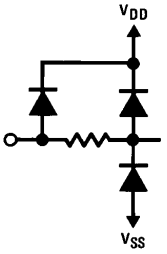
CD4001BC/BM



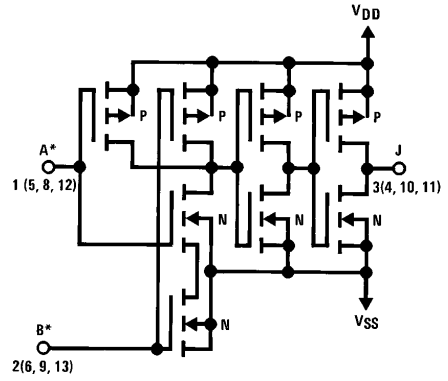
TL/F/5939–2

¼ of device shown

$J = \overline{A + B}$

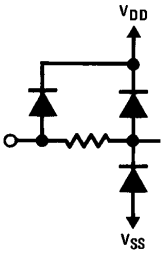
Logical "1" = High
Logical "0" = Low

All inputs protected by standard CMOS protection circuit.



TL/F/5939–5

CD4011BC/BM



TL/F/5939–6

¼ of device shown

$J = \overline{A \ B}$

Logical "1" = High
Logical "0" = Low

All inputs protected by standard CMOS protection circuit.

 TL/F/5939

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 and 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Voltage at any Pin	−0.5V to V_{DD} +0.5V
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
V_{DD} Range	−0.5 V_{DC} to +18 V_{DC}
Storage Temperature (T_S)	−65 C to +150 C
Lead Temperature (T_L) (Soldering, 10 seconds)	260 C

Operating Conditions

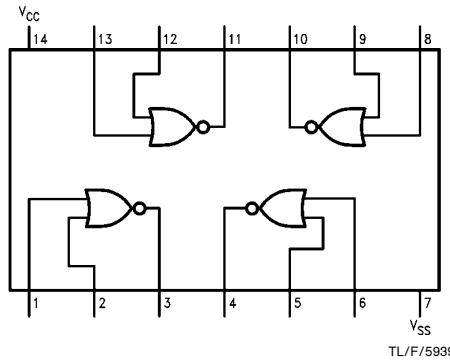
Operating Range (V_{DD})	3 V_{DC} to 15 V_{DC}
Operating Temperature Range	
CD4001BM, CD4011BM	−55 C to +125 C
CD4001BC, CD4011BC	−40 C to +85 C

DC Electrical Characteristics CD4001BM, CD4011BM (Note 2)

Symbol	Parameter	Conditions	−55 C		+25 C			+125 C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	V_{DD} = 5V, V_{IN} = V_{DD} or V_{SS}		0.25		0.004	0.25		7.5	A
		V_{DD} = 10V, V_{IN} = V_{DD} or V_{SS}		0.50		0.005	0.50		15	A
		V_{DD} = 15V, V_{IN} = V_{DD} or V_{SS}		1.0		0.006	1.0		30	A
V_{OL}	Low Level Output Voltage	V_{DD} = 5V, I_O < 1 A		0.05		0	0.05		0.05	V
		V_{DD} = 10V, I_O < 1 A		0.05		0	0.05		0.05	V
		V_{DD} = 15V, I_O < 1 A		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	V_{DD} = 5V, I_O < 1 A	4.95		4.95	5		4.95		V
		V_{DD} = 10V, I_O < 1 A	9.95		9.95	10		9.95		V
		V_{DD} = 15V, I_O < 1 A	14.95		14.95	15		14.95		V
V_{IL}	Low Level Input Voltage	V_{DD} = 5V, V_O = 4.5V		1.5		2	1.5		1.5	V
		V_{DD} = 10V, V_O = 9.0V		3.0		4	3.0		3.0	V
		V_{DD} = 15V, V_O = 13.5V		4.0		6	4.0		4.0	V
V_{IH}	High Level Input Voltage	V_{DD} = 5V, V_O = 0.5V	3.5		3.5	3		3.5		V
		V_{DD} = 10V, V_O = 1.0V	7.0		7.0	6		7.0		V
		V_{DD} = 15V, V_O = 1.5V	11.0		11.0	9		11.0		V
I_{OL}	Low Level Output Current (Note 3)	V_{DD} = 5V, V_O = 0.4V	0.64		0.51	0.88		0.36		mA
		V_{DD} = 10V, V_O = 0.5V	1.6		1.3	2.25		0.9		mA
		V_{DD} = 15V, V_O = 1.5V	4.2		3.4	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	V_{DD} = 5V, V_O = 4.6V	−0.64		−0.51	−0.88		−0.36		mA
		V_{DD} = 10V, V_O = 9.5V	−1.6		−1.3	−2.25		−0.9		mA
		V_{DD} = 15V, V_O = 13.5V	−4.2		−3.4	−8.8		−2.4		mA
I_{IN}	Input Current	V_{DD} = 15V, V_{IN} = 0V		−0.10		-10^{-5}	−0.10		−1.0	A
		V_{DD} = 15V, V_{IN} = 15V		0.10		10^{-5}	0.10		1.0	A

Connection Diagrams

CD4001BC/CD4001BM
Dual-In-Line Package



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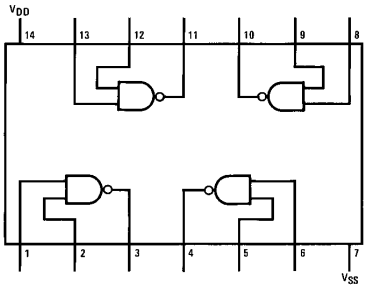
Top View

CD4011BC/CD4011BM
Dual-In-Line Package



TL/F/5939–4

Top View

Order Number CD4001B or CD4011B

DC Electrical Characteristics CD4001BC, CD4011BC (Note 2)

Symbol	Parameter	Conditions	−40 C		+25 C			+85 C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$, $V_{IN} = V_{DD}$ or V_{SS}		1		0.004	1		7.5	A
		$V_{DD} = 10V$, $V_{IN} = V_{DD}$ or V_{SS}		2		0.005	2		15	A
		$V_{DD} = 15V$, $V_{IN} = V_{DD}$ or V_{SS}		4		0.006	4		30	A
V_{OL}	Low Level Output Voltage	$V_{DD} = 5V$ } $I_O < 1$ A		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$ } $I_O < 1$ A		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$ } $I_O < 1$ A		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{DD} = 5V$ } $I_O < 1$ A	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$ } $I_O < 1$ A	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$ } $I_O < 1$ A	14.95		14.95	15		14.95		V
V_{IL}	Low Level Input Voltage	$V_{DD} = 5V$, $V_O = 4.5V$		1.5		2	1.5		1.5	V
		$V_{DD} = 10V$, $V_O = 9.0V$		3.0		4	3.0		3.0	V
		$V_{DD} = 15V$, $V_O = 13.5V$		4.0		6	4.0		4.0	V
V_{IH}	High Level Input Voltage	$V_{DD} = 5V$, $V_O = 0.5V$	3.5		3.5	3		3.5		V
		$V_{DD} = 10V$, $V_O = 1.0V$	7.0		7.0	6		7.0		V
		$V_{DD} = 15V$, $V_O = 1.5V$	11.0		11.0	9		11.0		V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 0.4V$	0.52		0.44	0.88		0.36		mA
		$V_{DD} = 10V$, $V_O = 0.5V$	1.3		1.1	2.25		0.9		mA
		$V_{DD} = 15V$, $V_O = 1.5V$	3.6		3.0	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 4.6V$	−0.52		−0.44	−0.88		−0.36		mA
		$V_{DD} = 10V$, $V_O = 9.5V$	−1.3		−1.1	−2.25		−0.9		mA
		$V_{DD} = 15V$, $V_O = 13.5V$	−3.6		−3.0	−8.8		−2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V$, $V_{IN} = 0V$		−0.30		-10^{-5}	−0.30		−1.0	A
		$V_{DD} = 15V$, $V_{IN} = 15V$		0.30		10^{-5}	0.30		1.0	A

AC Electrical Characteristics CD4001BC, CD4001BM

$T_A = 25$ C, Input t_r; $t_f = 20$ ns. $C_L = 50$ pF, $R_L = 200$k. Typical temperature coefficient is 0.3%/ C.

Symbol	Parameter	Conditions	Typ	Max	Units
t_{PHL}	Propagation Delay Time, High-to-Low Level	$V_{DD} = 5V$	120	250	ns
		$V_{DD} = 10V$	50	100	ns
		$V_{DD} = 15V$	35	70	ns
t_{PLH}	Propagation Delay Time, Low-to-High Level	$V_{DD} = 5V$	110	250	ns
		$V_{DD} = 10V$	50	100	ns
		$V_{DD} = 15V$	35	70	ns
t_{THL}, t_{TLH}	Transition Time	$V_{DD} = 5V$	90	200	ns
		$V_{DD} = 10V$	50	100	ns
		$V_{DD} = 15V$	40	80	ns
C_{IN}	Average Input Capacitance	Any Input	5	7.5	pF
C_{PD}	Power Dissipation Capacity	Any Gate	14		pF

AC Parameters are guaranteed by DC correlated testing.

Note 1: ''Absolute Maximum Ratings'' are those values beyond which the safety of the device cannot be guaranteed. Except for ''Operating Temperature Range'' they are not meant to imply that the devices should be operated at these limits. The table of ''Electrical Characteristics'' provides conditions for actual device operation.

Note 2: All voltages measured with respect to V_{SS} unless otherwise specified.

Note 3: I_{OL} and I_{OH} are tested one output at a time.

AC Electrical Characteristics CD4011BC, CD4011BM

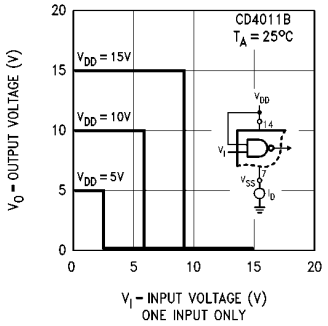
T_A = 25 C, Input t_r; t_f = 20 ns. C_L = 50 pF, R_L = 200k. Typical Temperature Coefficient is 0.3%/ C.

Symbol	Parameter	Conditions	Typ	Max	Units
t_{PHL}	Propagation Delay, High-to-Low Level	V_{DD} = 5V	120	250	ns
		V_{DD} = 10V	50	100	ns
		V_{DD} = 15V	35	70	ns
t_{PLH}	Propagation Delay, Low-to-High Level	V_{DD} = 5V	85	250	ns
		V_{DD} = 10V	40	100	ns
		V_{DD} = 15V	30	70	ns
t_{THL}, t_{TLH}	Transition Time	V_{DD} = 5V	90	200	ns
		V_{DD} = 10V	50	100	ns
		V_{DD} = 15V	40	80	ns
C_{IN}	Average Input Capacitance	Any Input	5	7.5	pF
C_{PD}	Power Dissipation Capacity	Any Gate	14		pF

AC Parameters are guaranteed by DC correlated testing.

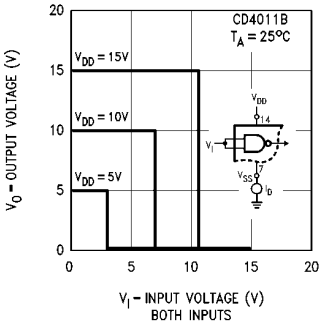
Typical Performance Characteristics

Typical Transfer Characteristics



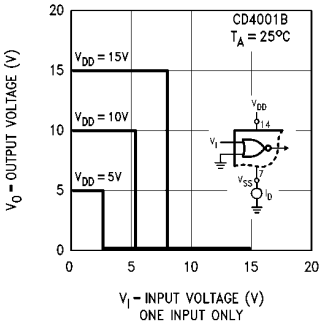
TL/F/5939–7

Typical Transfer Characteristics



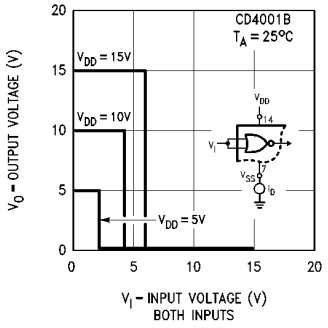
TL/F/5939–8

Typical Transfer Characteristics

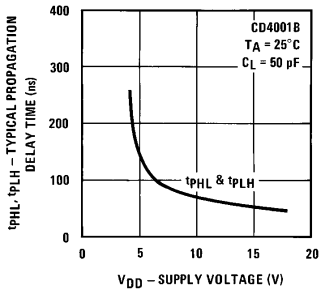


TL/F/5939–9

Typical Transfer Characteristics

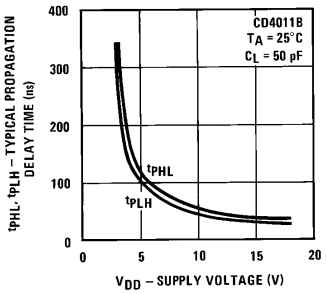


TL/F/5939–10



TL/F/5939–11

FIGURE 5



TL/F/5939–12

FIGURE 6

Datablad PC817

SHARP

PC817 Series

PC817 Series

High Density Mounting Type Photocoupler

✻ Lead forming type（I type ）and taping reel type （P type ）are also available.（**PC817I/PC817P** ）
✻✻ TÜV（VDE0884 ）approved type is also available as an option.

■ Features

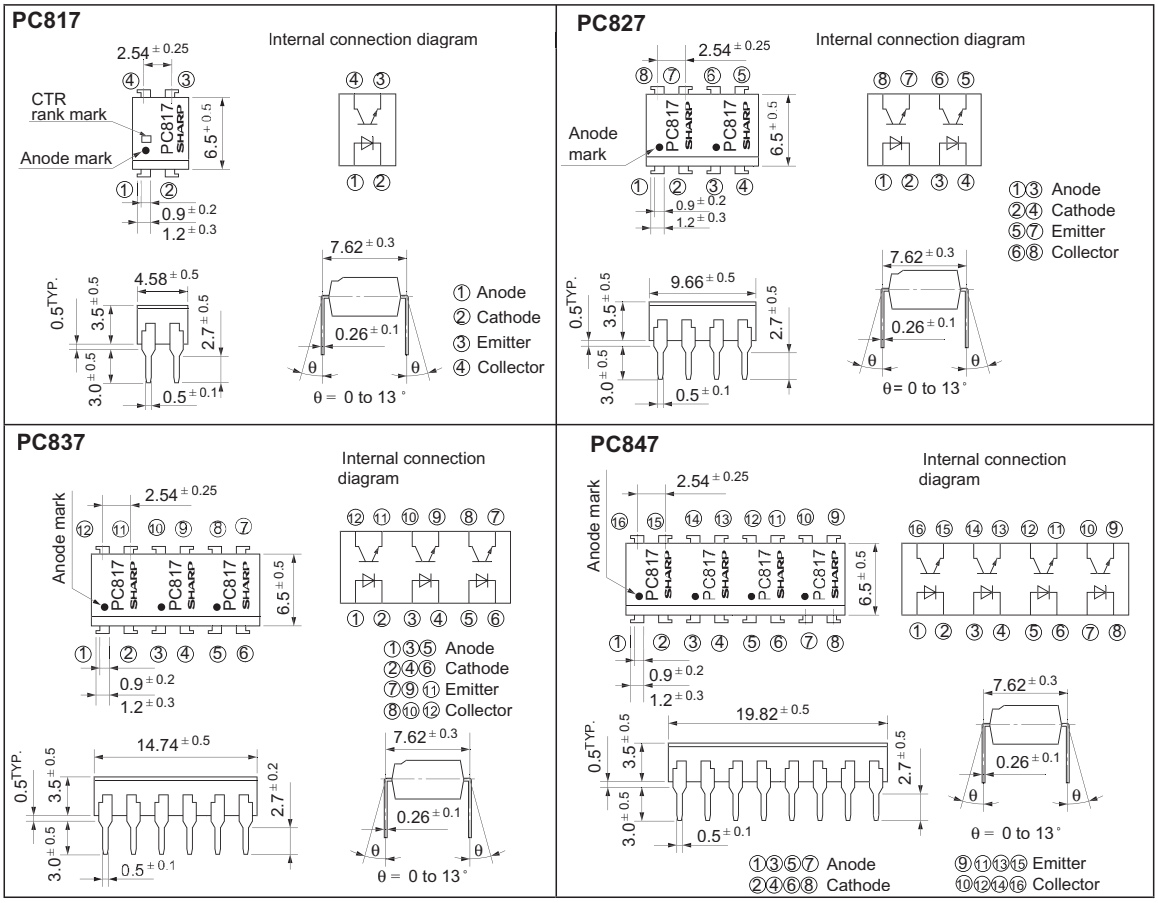
1. Current transfer ratio
   （CTR: MIN. 50% at I_F = 5mA ,V_{CE}=5V)
2. High isolation voltage between input and output（V_{iso} : 5 000V $_{rms}$）
3. Compact dual-in-line package
   PC817 : 1-channel type
   PC827 : 2-channel type
   PC837 : 3-channel type
   PC847 : 4-channel type
4. Recognized by UL, file No. E64380

■ Applications

1. Computer terminals
2. System appliances, measuring instruments
3. Registers, copiers, automatic vending machines
4. Electric home appliances, such as fan heaters, etc.
5. Signal transmission between circuits of different potentials and impedances

■ Outline Dimensions

（Unit : mm）



■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	*1Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P	70	mW
Output	Collector-emitter voltage	V_{CEO}	35	V
	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	I_C	50	mA
	Collector power dissipation	P_C	150	mW
Total power dissipation		P_{tot}	200	mW
*2Isolation voltage		V_{iso}	5 000	V_{rms}
Operating temperature		T_{opr}	- 30 to + 100	˚C
Storage temperature		T_{stg}	- 55 to + 125	˚C
*3Soldering temperature		T_{sol}	260	˚C

*1 Pulse width<=100μs, Duty ratio : 0.001
*2 40 to 60% RH, AC for 1 minute
*3 For 10 seconds

■ Electro-optical Characteristics (Ta= 25˚C)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		V_F	I_F = 20mA	-	1.2	1.4	V
	Peak forward voltage		V_{FM}	I_{FM} = 0.5A	-	-	3.0	V
	Reverse current		I_R	V_R = 4V	-	-	10	μA
	Terminal capacitance		C_t	V= 0, f= 1kHz	-	30	250	pF
Output	Collector dark current		I_{CEO}	V_{CE} = 20V	-	-	10^{-7}	A
Transfer characteristics	*4Current transfer ratio		CTR	I_F = 5mA, V_{CE} = 5V	50	-	600	%
	Collector-emitter saturation voltage		$V_{CE(sat)}$	I_F = 20mA, I_C = 1mA	-	0.1	0.2	V
	Isolation resistance		R_{ISO}	DC500V, 40 to 60% RH	5×10^{10}	10^{11}	-	Ω
	Floating capacitance		C_f	V= 0, f= 1MHz	-	0.6	1.0	pF
	Cut-off frequency		f_c	V_{CE} = 5V, I_C = 2mA, R_L = 100Ω, - 3dB	-	80	-	kHz
	Response time	Rise time	t_r	V_{CE} = 2V, I_C = 2mA, R_L = 100Ω	-	4	18	μs
		Fall time	t_f		-	3	18	μs

*4 Classification table of current transfer ratio is shown below.

Model No.	Rank mark	CTR (%)
PC817A	A	80 to 160
PC817B	B	130 to 260
PC817C	C	200 to 400
PC817D	D	300 to 600
PC8✻7AB	A or B	80 to 260
PC8✻7BC	B or C	130 to 400
PC8✻7CD	C or D	200 to 600
PC8✻7AC	A, B or C	80 to 400
PC8✻7BD	B, C or D	130 to 600
PC8✻7AD	A, B, C or D	80 to 600
PC8✻7	A, B, C, D or No mark	50 to 600

✻ : 1 or 2 or 3 or 4

Fig. 1 Forward Current vs. Ambient Temperature

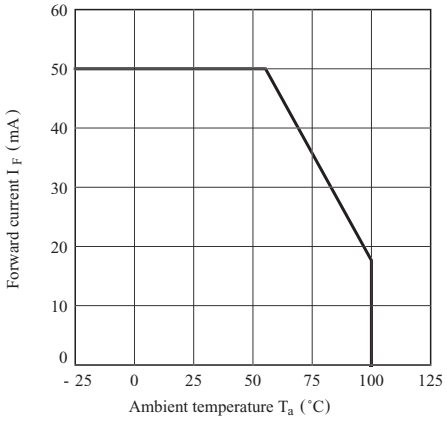


Fig. 2 Collector Power Dissipation vs. Ambient Temperature

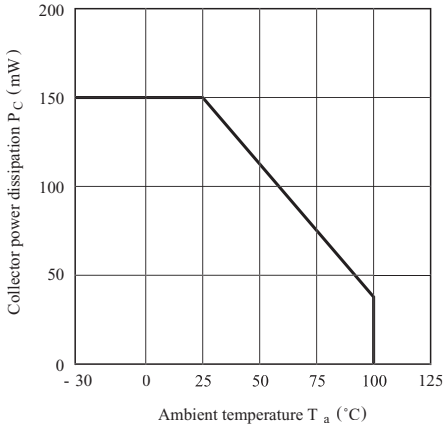


Fig. 3 Peak Forward Current vs. Duty Ratio

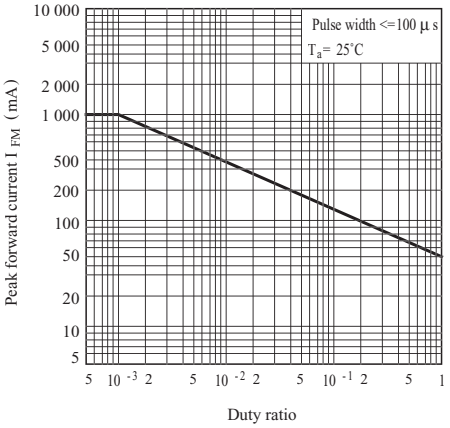


Fig. 4 Current Transfer Ratio vs. Forward Current

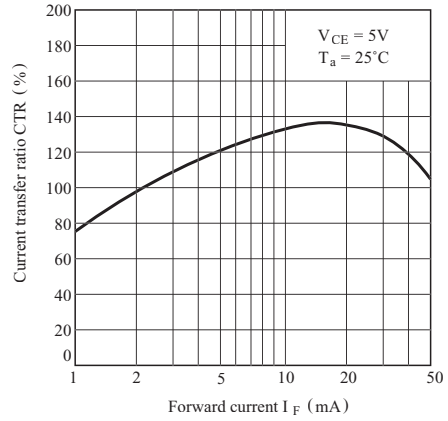


Fig. 5 Forward Current vs. Forward Voltage

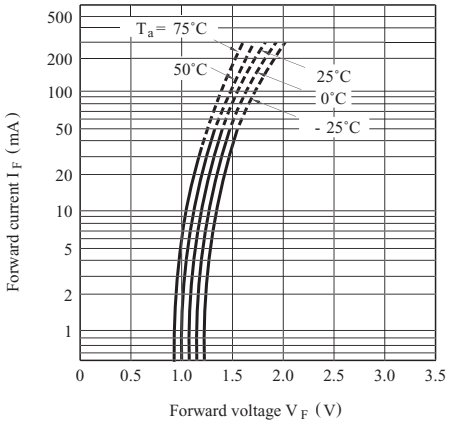


Fig. 6 Collector Current vs. Collector-emitter Voltage

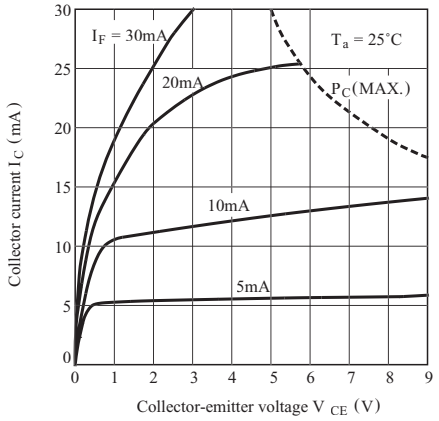


Fig. 7 Relative Current Transfer Ratio vs. Ambient Temperature

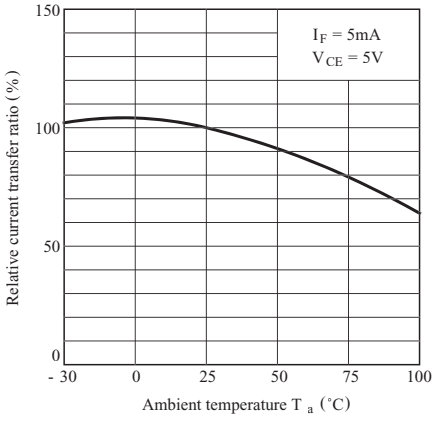


Fig. 8 Collector-emitter Saturation Voltage vs. Ambient Temperature

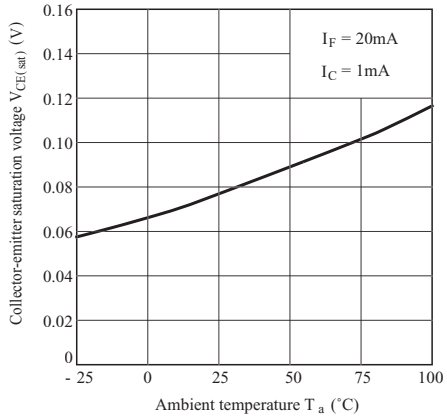


Fig. 9 Collector Dark Current vs. Ambient Temperature

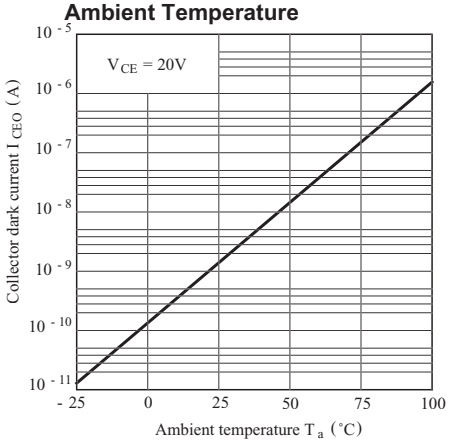


Fig.10 Response Time vs. Load Resistance

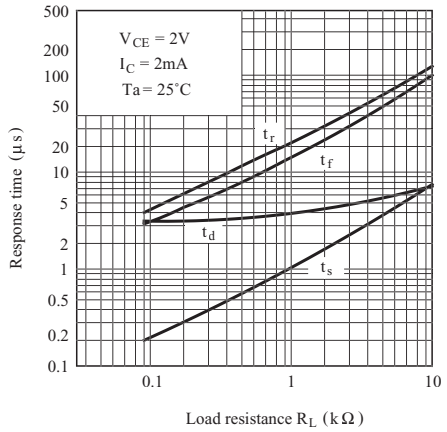
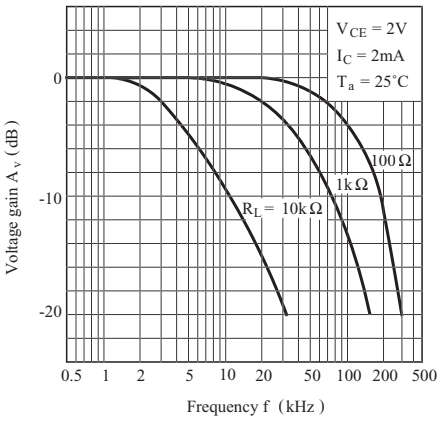
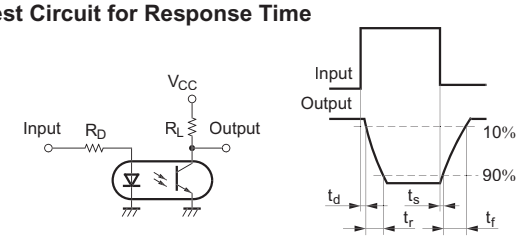


Fig.11 Frequency Response



Test Circuit for Response Time



Test Circuit for Frequency Response

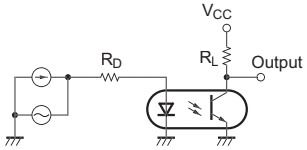
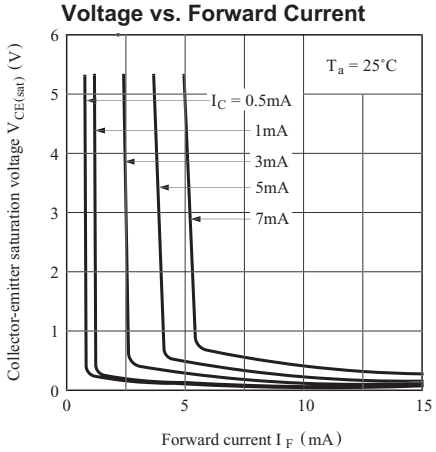


Fig.12 Collector-emitter Saturation Voltage vs. Forward Current



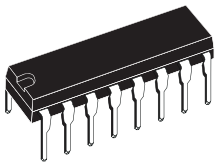
● Please refer to the chapter "Precautions for Use"

Datablad ULN2001A-4A

ULN2001A-ULN2002A
ULN2003A-ULN2004A

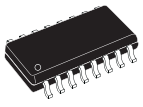
SEVEN DARLINGTON ARRAYS

- SEVEN DARLINGTONS PER PACKAGE
- OUTPUT CURRENT 500mA PER DRIVER (600mA PEAK)
- OUTPUT VOLTAGE 50V
- INTEGRATED SUPPRESSION DIODES FOR INDUCTIVE LOADS
- OUTPUTS CAN BE PARALLELED FOR HIGHER CURRENT
- TTL/CMOS/PMOS/DTL COMPATIBLE INPUTS
- INPUTS PINNED OPPOSITE OUTPUTS TO SIMPLIFY LAYOUT



DIP16

ORDERING NUMBERS: ULN2001A/2A/3A/4A



SO16

ORDERING NUMBERS: ULN2001D/2D/3D/4D

DESCRIPTION

The ULN2001A, ULN2002A, ULN2003 and ULN2004A are high voltage, high current darlington arrays each containing seven open collector darlington pairs with common emitters. Each channel rated at 500mA and can withstand peak currents of 600mA. Suppression diodes are included for inductive load driving and the inputs are pinned opposite the outputs to simplify board layout.

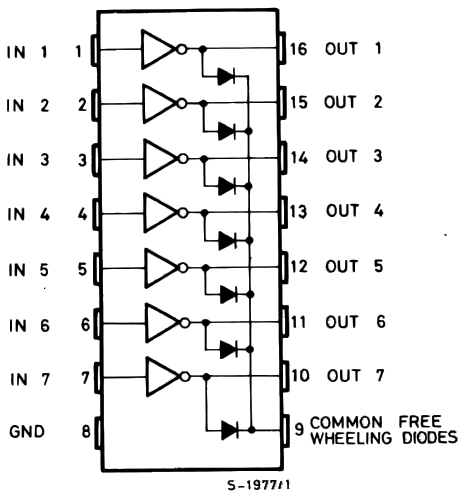
The four versions interface to all common logic families :

ULN2001A	General Purpose, DTL, TTL, PMOS, CMOS
ULN2002A	14-25V PMOS
ULN2003A	5V TTL, CMOS
ULN2004A	6–15V CMOS, PMOS

These versatile devices are useful for driving a wide range of loads including solenoids, relays DC motors, LED displays filament lamps, thermal printheads and high power buffers.

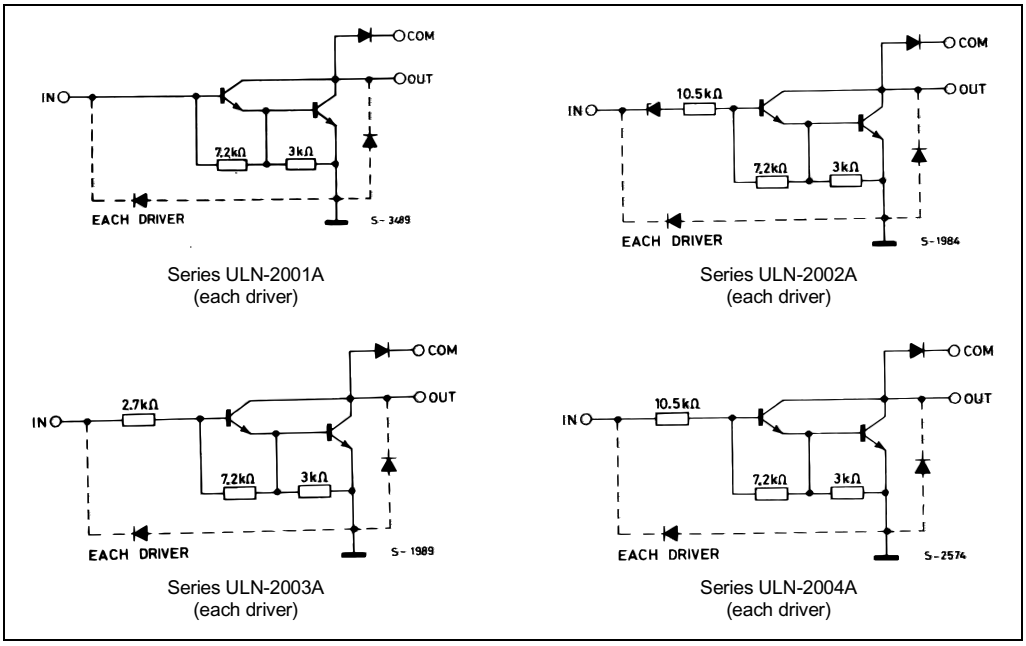
The ULN2001A/2002A/2003A and 2004A are supplied in 16 pin plastic DIP packages with a copper leadframe to reduce thermal resistance. They are available also in small outline package (SO-16) as ULN2001D/2002D/2003D/2004D.

PIN CONNECTION



ULN2001A - ULN2002A - ULN2003A - ULN2004A

SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_o	Output Voltage	50	V
V_{in}	Input Voltage (for ULN2002A/D - 2003A/D - 2004A/D)	30	V
I_c	Continuous Collector Current	500	mA
I_b	Continuous Base Current	25	mA
T_{amb}	Operating Ambient Temperature Range	– 20 to 85	°C
T_{stg}	Storage Temperature Range	– 55 to 150	°C
T_j	Junction Temperature	150	°C

THERMAL DATA

Symbol	Parameter		DIP16	SO16	Unit
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	Max.	70	120	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	Fig.
I_{CEX}	Output Leakage Current	V_{CE} = 50V T_{amb} = 70°C, V_{CE} = 50V T_{amb} = 70°C for ULN2002A V_{CE} = 50V, V_i = 6V for ULN2004A V_{CE} = 50V, V_i = 1V			50 100 500 500	µA µA µA µA	1a 1a 1b 1b
$V_{CE(sat)}$	Collector-emitter Saturation Voltage	I_C = 100mA, I_B = 250µA I_C = 200 mA, I_B = 350µA I_C = 350mA, I_B = 500µA		0.9 1.1 1.3	1.1 1.3 1.6	V V V	2 2 2
$I_{i(on)}$	Input Current	for ULN2002A, V_i = 17V for ULN2003A, V_i = 3.85V for ULN2004A, V_i = 5V V_i = 12V		0.82 0.93 0.35 1	1.25 1.35 0.5 1.45	mA mA mA mA	3 3 3 3
$I_{i(off)}$	Input Current	T_{amb} = 70°C, I_C = 500µA	50	65		µA	4
$V_{i(on)}$	Input Voltage	V_{CE} = 2V for ULN2002A I_C = 300mA for ULN2003A I_C = 200mA I_C = 250mA I_C = 300mA for ULN2004A I_C = 125mA I_C = 200mA I_C = 275mA I_C = 350mA			 13 2.4 2.7 3 5 6 7 8	V	5
h_{FE}	DC Forward Current Gain	for ULN2001A V_{CE} = 2V, I_C = 350mA	1000				2
C_i	Input Capacitance			15	25	pF	
t_{PLH}	Turn-on Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
t_{PHL}	Turn-off Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
I_R	Clamp Diode Leakage Current	V_R = 50V T_{amb} = 70°C, V_R = 50V			50 100	µA µA	6 6
V_F	Clamp Diode Forward Voltage	I_F = 350mA		1.7	2	V	7

Datablad 74HC132

FAIRCHILD SEMICONDUCTOR TM

September 1983
Revised February 1999

MM74HC132
Quad 2-Input NAND Schmitt Trigger

General Description

The MM74HC132 utilizes advanced silicon-gate CMOS technology to achieve the low power dissipation and high noise immunity of standard CMOS, as well as the capability to drive 10 LS-TTL loads.

The 74HC logic family is functionally and pinout compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 12 ns
- Wide power supply range: 2V–6V
- Low quiescent current: 20 μA maximum (74HC Series)
- Low input current: 1 μA maximum
- Fanout of 10 LS-TTL loads
- Typical hysteresis voltage: 0.9V at V_{CC}=4.5V

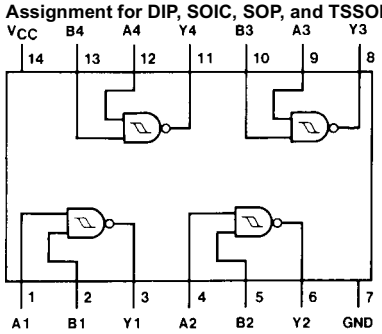
Ordering Code:

Order Number	Package Number	Package Description
MM74HC132M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150” Narrow Body
MM74HC132SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC132MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC132N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300” Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter “X” to the ordering code. (Tape and Reel not available in N14A.)

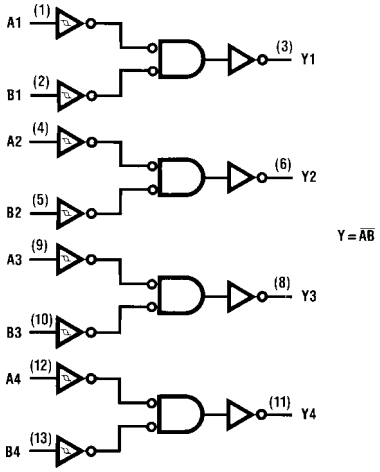
Connection Diagram

Pin Assignment for DIP, SOIC, SOP, and TSSOP



Top View

Logic Diagram



Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temperature Range (T_A)	−40	+125	°C

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: –

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions		V_{CC}	T_A = 25°C	T_A = -40 to 85°C	T_A = -40 to 125°C	Units
					Typ	Guaranteed Limits		
V_{T+}	Positive Going Threshold Voltage		Min	2.0V		1.0	1.0	1.0	V
				4.5V		2.0	2.0	2.0	V
				6.0V		3.0	3.0	3.0	V
			Max	2.0V		1.5	1.5	1.5	V
				4.5V		3.15	3.15	3.15	V
				6.0V		4.2	4.2	4.2	V
V_{T-}	Negative Going Threshold Voltage		Min	2.0V		0.3	0.3	0.3	V
				4.5V		0.9	0.9	0.9	V
				6.0V		1.2	1.2	1.2	V
			Max	2.0V		1.0	1.0	1.0	V
				4.5V		2.2	2.2	2.2	V
				6.0V		3.0	3.0	3.0	V
V_H	Hysteresis Voltage		Min	2.0V		0.2	0.2	0.2	V
				4.5V		0.4	0.4	0.4	V
				6.0V		0.5	0.5	0.5	V
			Max	2.0V		1.0	1.0	1.0	V
				4.5V		1.4	1.4	1.4	V
				6.0V		1.5	1.5	1.5	V
V_{OH}	Minimum HIGH Level Output Voltage	V_{IN} = V_{IH} or V_{IL}		2.0V	2.0	1.9	1.9	1.9	V
		$\|I_{OUT}\| \leq 20$ μA		4.5V	4.5	4.4	4.4	4.4	V
		V_{IN} = V_{IH} or V_{IL}		6.0V	6.0	5.9	5.9	5.9	V
		$\|I_{OUT}\| \leq 4.0$ mA		4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \leq 5.2$ mA		6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum LOW Level Output Voltage	V_{IN} = V_{IH} or V_{IL}		2.0V	0	0.1	0.1	0.1	V
		$\|I_{OUT}\| \leq 20$ μA		4.5V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL}		6.0V	0	0.1	0.1	0.1	V
		$\|I_{OUT}\| \leq 4.0$ mA		4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \leq 5.2$ mA		6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND		6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND		6.0V		2.0	20	40	μA
		I_{OUT} = 0 μA							

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics

V_{CC} = 5V, T_A = 25°C, C_L = 15 pF, $t_r = t_f$ = 6 ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		12	20	ns

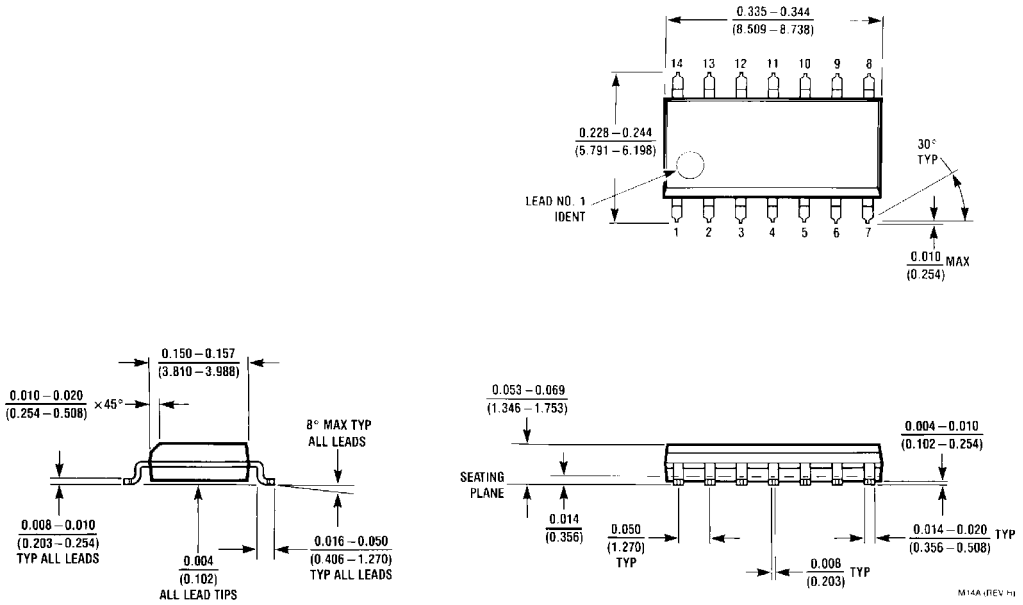
AC Electrical Characteristics

V_{CC} = 2.0V to 6.0V, C_L = 50 pF, $t_r = t_f$ = 6 ns (unless otherwise specified)

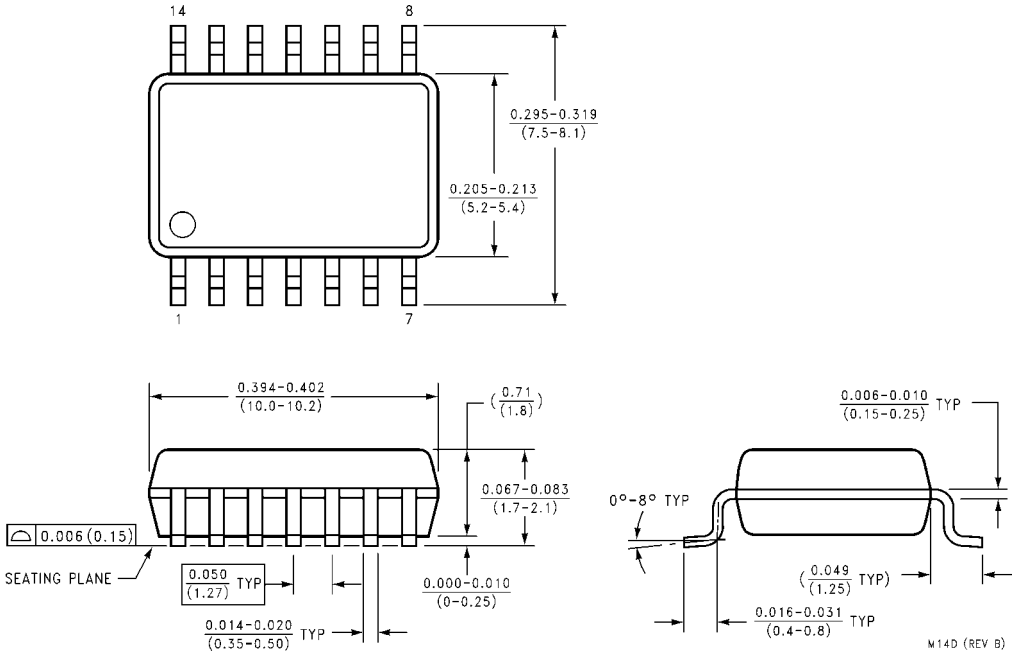
Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	63	125	158	186	ns
			4.5V	13	25	32	37	ns
			6.0V	11	21	27	32	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		130				pF
C_{IN}	Maximum Input Capacitance				5	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters) unless otherwise noted



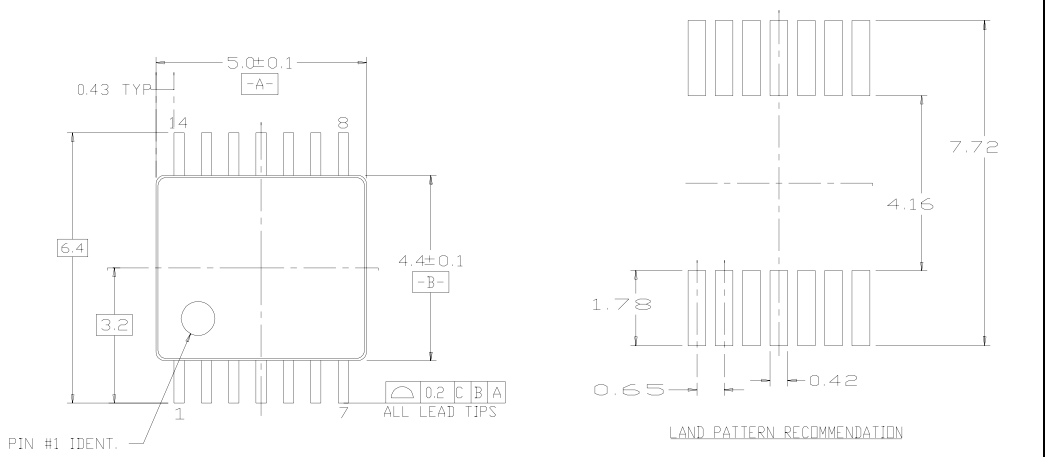
14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150" Narrow Body
Package Number M14A

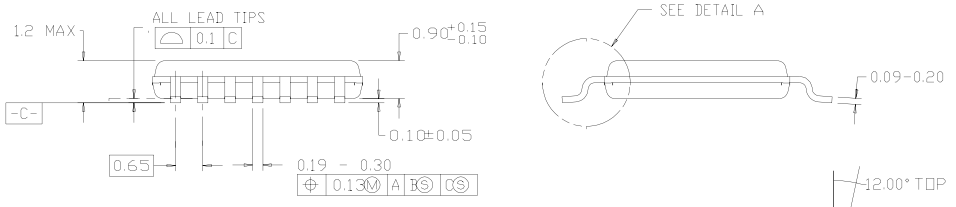


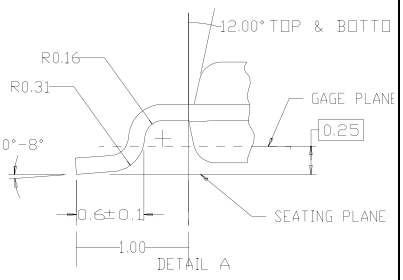
14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
Package Number M14D

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)

14LD, TSSOP, JEDEC MO-153, 4.4MM WIDE







NOTES:

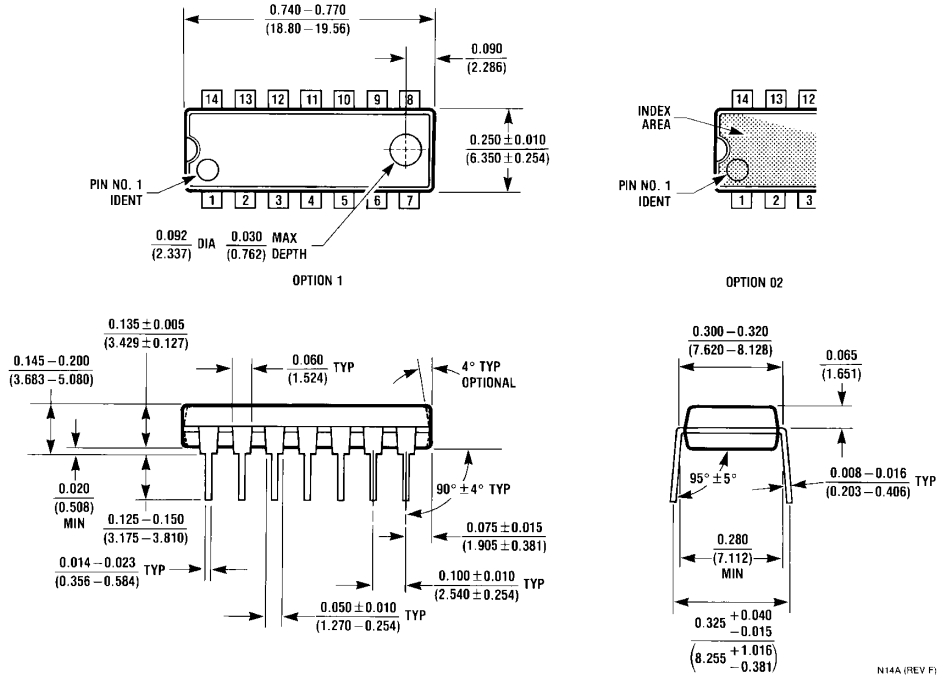
A. CONFORMS TO JEDEC REGISTRATION MO-153, VARIATION AB, REF NOTE 6, DATED 7/93

B. DIMENSIONS ARE IN MILLIMETERS

C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS

14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
Package Number MTC14

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
Package Number N14A

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Datablad 74HC/HCT138

INTEGRATED CIRCUITS

DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Information
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Outlines

74HC/HCT138
3-to-8 line decoder/demultiplexer; inverting

Product specification
File under Integrated Circuits, IC06

September 1993

Philips Semiconductors

PHILIPS

3-to-8 line decoder/demultiplexer; inverting 74HC/HCT138

FEATURES

- Demultiplexing capability
- Multiple input enable for easy expansion
- Ideal for memory chip select decoding
- Active LOW mutually exclusive outputs
- Output capability: standard
- I_{CC} category: MSI

GENERAL DESCRIPTION

The 74HC/HCT138 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT138 decoders accept three binary weighted address inputs (A_0, A_1, A_2) and when enabled, provide 8 mutually exclusive active LOW outputs ($\overline{Y}_0$ to $\overline{Y}_7$).

The “138” features three enable inputs: two active LOW ($\overline{E}_1$ and $\overline{E}_2$) and one active HIGH (E_3). Every output will be HIGH unless $\overline{E}_1$ and $\overline{E}_2$ are LOW and E_3 is HIGH.

This multiple enable function allows easy parallel expansion of the “138” to a 1-of-32 (5 lines to 32 lines) decoder with just four “138” ICs and one inverter.

The ”138” can be used as an eight output demultiplexer by using one of the active LOW enable inputs as the data input and the remaining enable inputs as strobes. Unused enable inputs must be permanently tied to their appropriate active HIGH or LOW state.

The ”138” is identical to the “238” but has inverting outputs.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f$ = 6 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC	HCT	
	propagation delay	C_L = 15 pF; V_{CC} = 5 V			
t_{PHL}/ t_{PLH}	A_n to $\overline{Y}_n$		12	17	ns
t_{PHL}/ t_{PLH}	E_3 to $\overline{Y}_n$ $\overline{E}_n$ to $\overline{Y}_n$		14	19	ns
C_I	input capacitance		3.5	3.5	pF
C_{PD}	power dissipation capacitance per package	notes 1 and 2	67	67	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in µW):

   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

   f_i = input frequency in MHz

   f_o = output frequency in MHz

   $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

   C_L = output load capacitance in pF

   V_{CC} = supply voltage in V

2. For HC the condition is V_I = GND to V_{CC}
   For HCT the condition is V_I = GND to V_{CC} − 1.5 V

ORDERING INFORMATION

See *“74HC/HCT/HCU/HCMOS Logic Package Information”*.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1, 2, 3	A_0 to A_2	address inputs
4, 5	$\overline{E}_1$, $\overline{E}_2$	enable inputs (active LOW)
6	E_3	enable input (active HIGH)
8	GND	ground (0 V)
15, 14, 13, 12, 11, 10, 9, 7	$\overline{Y}_0$ to $\overline{Y}_7$	outputs (active LOW)
16	V_{CC}	positive supply voltage

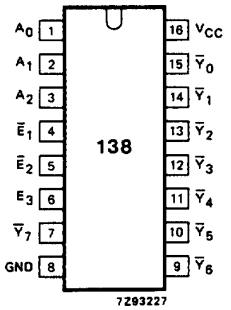


Fig.1 Pin configuration.

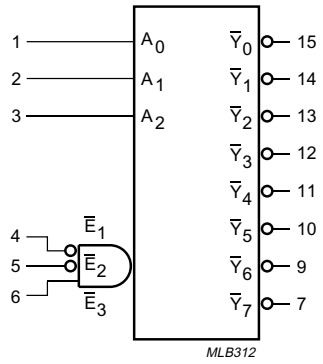
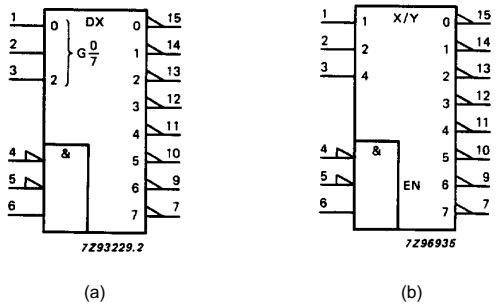


Fig.2 Logic symbol.



(a) (b)

Fig.3 IEC logic symbol.

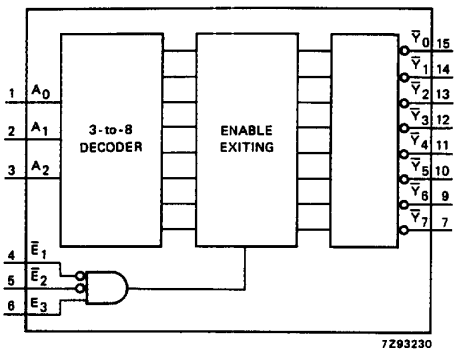


Fig.4 Functional diagram.

FUNCTION TABLE

INPUTS						OUTPUTS							
$\overline{E}_1$	$\overline{E}_2$	E_3	A_0	A_1	A_2	$\overline{Y}_0$	$\overline{Y}_1$	$\overline{Y}_2$	$\overline{Y}_3$	$\overline{Y}_4$	$\overline{Y}_5$	$\overline{Y}_6$	$\overline{Y}_7$
H	X	X	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	L	X	X	X	H	H	H	H	H	H	H	H
L	L	H	L	L	L	L	H	H	H	H	H	H	H
L	L	H	H	L	L	H	L	H	H	H	H	H	H
L	L	H	L	H	L	H	H	L	H	H	H	H	H
L	L	H	H	H	L	H	H	H	L	H	H	H	H
L	L	H	L	L	H	H	H	H	H	L	H	H	H
L	L	H	H	L	H	H	H	H	H	H	L	H	H
L	L	H	L	H	H	H	H	H	H	H	H	L	H
L	L	H	H	H	H	H	H	H	H	H	H	H	L

Notes

1. H = HIGH voltage level
   L = LOW voltage level
   X = don't care

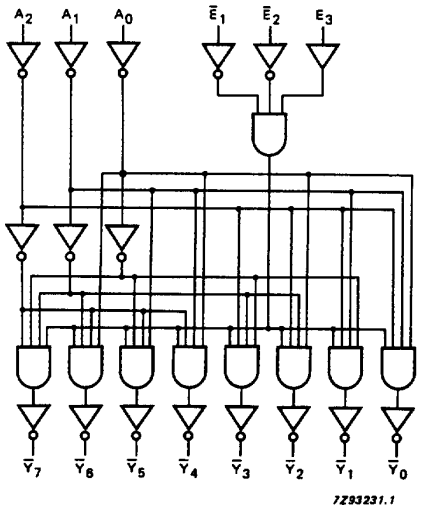


Fig.5 Logic diagram.

DC CHARACTERISTICS FOR 74HC

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: MSI

AC CHARACTERISTICS FOR 74HC

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HC								V_{CC} (V)	WAVEFORMS
		+25			−40 to +85		−40 to +125				
		min.	typ.	max.	min.	max.	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay A_n to $\overline{Y}_n$		41 15 12	150 30 26		190 38 33		225 45 38	ns	2.0 4.5 6.0	Fig.6
t_{PHL}/ t_{PLH}	propagation delay E_3 to $\overline{Y}_n$		47 17 14	150 30 26		190 38 33		225 45 38	ns	2.0 4.5 6.0	Fig.6
t_{PHL}/ t_{PLH}	propagation delay $\overline{E}_n$ to $\overline{Y}_n$		47 17 14	150 30 26		190 38 33		225 45 38	ns	2.0 4.5 6.0	Fig.7
t_{THL}/ t_{TLH}	output transition time		19 7 6	75 15 13		95 19 16		110 22 19	ns	2.0 4.5 6.0	Figs 6 and 7

DC CHARACTERISTICS FOR 74HCT

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: MSI

Note to HCT types

The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given in the family specifications. To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

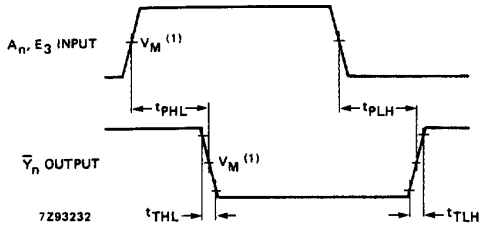
INPUT	UNIT LOAD COEFFICIENT
A_n	1.50
$\overline{E}_n$	1.25
E_3	1.00

AC CHARACTERISTICS FOR 74HCT

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

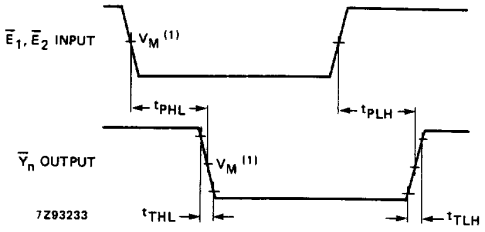
SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HCT								V_{CC} (V)	WAVEFORMS
		+25			−40 to +85		−40 to +125				
		min.	typ.	max.	min.	max.	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay A_n to $\overline{Y}_n$		20	35		44		53	ns	4.5	Fig.6
t_{PHL}/ t_{PLH}	propagation delay E_3 to $\overline{Y}_n$		18	40		50		60	ns	4.5	Fig.6
t_{PHL}/ t_{PLH}	propagation delay $\overline{E}_n$ to $\overline{Y}_n$		19	40		50		60	ns	4.5	Fig.7
t_{THL}/ t_{TLH}	output transition time		7	15		19		22	ns	4.5	Figs 6 and 7

AC WAVEFORMS



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.6 Waveforms showing the address input (A_n) and enable input (E_3) to output ($\overline{Y}_n$) propagation delays and the output transition times.



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.7 Waveforms showing the enable input ($\overline{E}_n$) to output ($\overline{Y}_n$) propagation delays and the output transition times.

PACKAGE OUTLINES

See *"74HC/HCT/HCU/HCMOS Logic Package Outlines"*.

Datablad 74HC/HCT74

INTEGRATED CIRCUITS

DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications

74HC/HCT74
Dual D-type flip-flop with set and reset; positive-edge trigger

Product specification
Supersedes data of September 1993
File under Integrated Circuits, IC06

1998 Feb 23

Philips
Semiconductors

PHILIPS

Dual D-type flip-flop with set and reset; positive-edge trigger

74HC/HCT74

FEATURES

- Output capability: standard
- I_{CC} category: flip-flops

GENERAL DESCRIPTION

The 74HC/HCT74 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT74 are dual positive-edge triggered, D-type flip-flops with individual data (D) inputs, clock (CP) inputs, set ($\overline{S}_D$) and reset ($\overline{R}_D$) inputs; also complementary Q and $\overline{Q}$ outputs.

The set and reset are asynchronous active LOW inputs and operate independently of the clock input. Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D inputs must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f$ = 6 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC	HCT	
t_{PHL}/ t_{PLH}	propagation delay	C_L = 15 pF; V_{CC} = 5 V			
	nCP to nQ, n$\overline{Q}$		14	15	ns
	n$\overline{S}_D$ to nQ, n$\overline{Q}$		15	18	ns
	n$\overline{R}_D$ to nQ, n$\overline{Q}$		16	18	ns
f_{max}	maximum clock frequency		76	59	MHz
C_I	input capacitance		3.5	3.5	pF
C_{PD}	power dissipation capacitance per flip-flop	notes 1 and 2	24	29	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

   f_i = input frequency in MHz

   f_o = output frequency in MHz

   $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

   C_L = output load capacitance in pF

   V_{CC} = supply voltage in V
2. For HC the condition is V_I = GND to V_{CC}

   For HCT the condition is V_I = GND to V_{CC} – 1.5 V

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
74HC(T)74N	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HC(T)74D	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74HCT74DB	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74HCT74PW	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1, 13	$1\overline{R}_D$, $2\overline{R}_D$	asynchronous reset-direct input (active LOW)
2, 12	1D, 2D	data inputs
3, 11	1CP, 2CP	clock input (LOW-to-HIGH, edge-triggered)
4, 10	$1\overline{S}_D$, $2\overline{S}_D$	asynchronous set-direct input (active LOW)
5, 9	1Q, 2Q	true flip-flop outputs
6, 8	$1\overline{Q}$, $2\overline{Q}$	complement flip-flop outputs
7	GND	ground (0 V)
14	V_{CC}	positive supply voltage

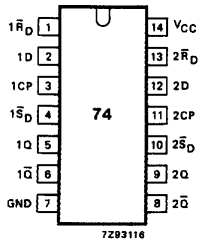


Fig.1 Pin configuration.

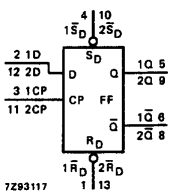


Fig.2 Logic symbol.

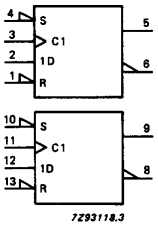


Fig.3 IEC logic symbol.

Dual D-type flip-flop with set and reset; positive-edge trigger

74HC/HCT74

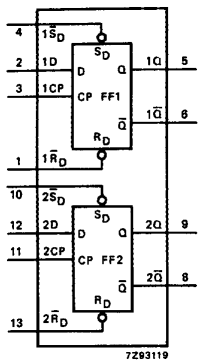


Fig.4 Functional diagram.

FUNCTION TABLE

INPUTS				OUTPUTS	
$\overline{S}_D$	$\overline{R}_D$	CP	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H	H

INPUTS				OUTPUTS	
$\overline{S}_D$	$\overline{R}_D$	CP	D	Q_{n+1}	$\overline{Q}_{n+1}$
H	H	↑	L	L	H
H	H	↑	H	H	L

Note

1. H = HIGH voltage level
   L = LOW voltage level
   X = don't care
   ↑ = LOW-to-HIGH CP transition
   Q_{n+1} = state after the next LOW-to-HIGH CP transition

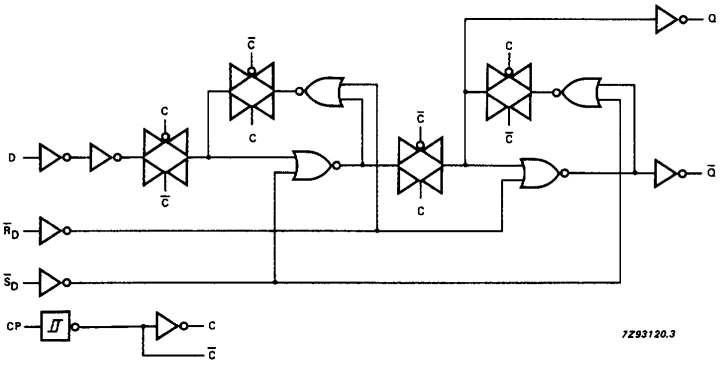


Fig.5 Logic diagram (one flip-flop).

DC CHARACTERISTICS FOR 74HC

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: flip-flops

AC CHARACTERISTICS

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HC									
		+25			−40 to +85		−40 to +125			V_{CC} (V)	WAVEFORMS
		min.	typ.	max.	min.	max	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay nCP to nQ, n$\overline{Q}$		47	175		220		265	ns	2.0	Fig.6
			17	35		44		53		4.5	
			14	30		37		45		6.0	
t_{PHL}/ t_{PLH}	propagation delay n$\overline{S}_D$ to nQ, n$\overline{Q}$		50	200		250		300	ns	2.0	Fig.7
			18	40		50		60		4.5	
			14	34		43		51		6.0	
t_{PHL}/ t_{PLH}	propagation delay n$\overline{R}_D$ to nQ, n$\overline{Q}$		52	200		250		300	ns	2.0	Fig.7
			19	40		50		60		4.5	
			15	34		43		51		6.0	
t_{THL}/ t_{TLH}	output transition time		19	75		95		110	ns	2.0	Fig.6
			7	15		19		22		4.5	
			6	13		16		19		6.0	
t_W	clock pulse width HIGH or LOW	80	19		100		120		ns	2.0	Fig.6
		16	7		20		24			4.5	
		14	6		17		20			6.0	
t_W	set or reset pulse width LOW	80	19		100		120		ns	2.0	Fig.7
		16	7		20		24			4.5	
		14	6		17		20			6.0	
t_{rem}	removal time set or reset	30	3		40		45		ns	2.0	Fig.7
		6	1		8		9			4.5	
		5	1		7		8			6.0	
t_{su}	set-up time nD to nCP	60	6		75		90		ns	2.0	Fig.6
		12	2		15		18			4.5	
		10	2		13		15			6.0	
t_h	hold time nCP to nD	3	−6		3		3		ns	2.0	Fig.6
		3	−2		3		3			4.5	
		3	−2		3		3			6.0	
f_{max}	maximum clock pulse frequency	6.0	23		4.8		4.0		MHz	2.0	Fig.6
		30	69		24		20			4.5	
		35	82		28		24			6.0	

DC CHARACTERISTICS FOR 74HCT

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: flip-flops

Note to HCT types

The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given in the family specifications. To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

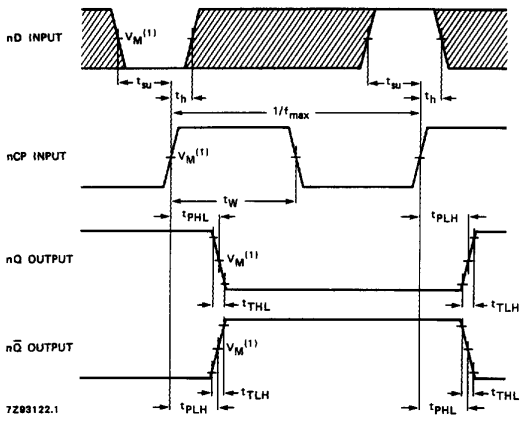
INPUT	UNIT LOAD COEFFICIENT
nD	0.70
$n\overline{R}_D$	0.70
$n\overline{S}_D$	0.80
nCP	0.80

AC CHARACTERISTICS FOR 74HCT

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HCT								V_{CC} (V)	WAVEFORMS
		+25			−40 to +85		−40 to +125				
		min.	typ.	max.	min.	max.	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay nCP to nQ, $n\overline{Q}$		18	35		44		53	ns	4.5	Fig.6
t_{PHL}/ t_{PLH}	propagation delay $n\overline{S}_D$ to nQ, $n\overline{Q}$		23	40		50		60	ns	4.5	Fig.7
t_{PHL}/ t_{PLH}	propagation delay $n\overline{R}_D$ to nQ, $n\overline{Q}$		24	40		50		60	ns	4.5	Fig.7
t_{THL}/ t_{TLH}	output transition time		7	15		19		22	ns	4.5	Fig.6
t_W	clock pulse width HIGH or LOW	18	9		23		27		ns	4.5	Fig.6
t_W	set or reset pulse width LOW	16	9		20		24		ns	4.5	Fig.7
t_{rem}	removal time set or reset	6	1		8		9		ns	4.5	Fig.7
t_{su}	set-up time nD to nCP	12	5		15		18		ns	4.5	Fig.6
t_h	hold time nCP to nD	3	−3		3		3		ns	4.5	Fig.6
f_{max}	maximum clock pulse frequency	27	54		22		18		MHz	4.5	Fig.6

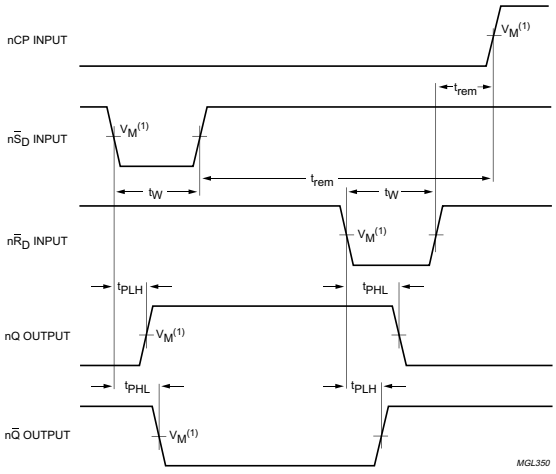
AC WAVEFORMS



The shaded areas indicate when the input is permitted to change for predictable output performance.

(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.6 Waveforms showing the clock (nCP) to output (nQ, nQ̄) propagation delays, the clock pulse width, the nD to nCP set-up, the nCP to nD hold times, the output transition times and the maximum clock pulse frequency.



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.7 Waveforms showing the set ($n\overline{S}_D$) and reset ($n\overline{R}_D$) input to output (nQ, nQ̄) propagation delays, the set and reset pulse widths and the $n\overline{R}_D$, $n\overline{S}_D$ to nCP removal time.